WE CLAIM AS OUR INVENTION:

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1	1)	Α	microsampling	device	comprising:
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- a substrate defining a microsampler chamber; and
- a cuvette window formed of silicon nitride.
- 1 2) The device of Claim 1 wherein the substrate is silicon.
- 1 3) The device of Claim 2 wherein the silicon substrate has a thickness of approximately 500 micrometers.
 - 4) The device of Claim 1 wherein the silicon nitride window has a thickness of approximately 0.01 to 5 micrometers.
 - 5) The device of Claim 1 wherein the chamber has a volume of less than 1 micrometer.

	1	6) A method of constructing a cuvette window in the microsampler								
H. H. B. Span Land Bear H. Br. of Duris china Grant H. B. Span H. B. Brand Bear H. B. Brand Bear H. B. Brand Bear H. Brand Bear H. Brand Bear H. Span H. B. Brand Bear H.	2	chamber of a microsampling device, the method comprising providing a silicon wafer having a top surface and a								
	3									
	4	bottom surface;								
	5	etching a patterned depression in the top surface of the								
	6	silicon wafer thereby defining the microsampler chamber;								
	7	depositing a silicon nitride film on the top surface of								
	8	the silicon wafer; and								
	9	etching a patterned depression in the bottom surface of								
	10	the silicon wafer and exposing the silicon nitride film forming								
	11	the window.								
	1	7) The method of Claim 6 wherein the silicon wafer has a								
	2	thickness of approximately 500 micrometers.								
	1	8) The method of Claim 6 wherein the silicon nitride film has a								
	2	thickness of approximately 0.01 to 5 micrometers.								

- 9) A silicon device comprising:
- a silicon substrate defining a cuvette; and
- a cuvette window formed of silicon nitride.
- 1 10) The device of Claim 9 wherein the silicon nitride window has
- a thickness of approximately 0.01 to 5 micrometers.

A. Bong oding than the transfer of the transfe	1	11)A method of constructing a window in the cuvette of a silicon
	2	device, the method comprising
	3	providing a silicon substrate having a top surface and a
	4	bottom surface;
	5	etching a patterned depression in the top surface of the
	6	silicon wafer thereby defining the cuvette;
	7	depositing a silicon nitride film on the top surface of
	8	the silicon wafer; and
	9	etching a patterned depression in the bottom surface of
	10	the silicon wafer and exposing the silicon nitride film forming
	11	the window.
	1	12) The method of Claim 12 wherein the substrate is a silicon
, P. M.	2	wafer.
B H S Conf. conf. Ton. B H. B.		13) The method of Claim 12 wherein the silicon nitride film has a
		thickness of approximately 0.01 to 5 micrometers.